IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Claims 1-13 (Canceled)

Claim 14. (Currently Amended) A manufacturing method of field emission type cold cathode device comprising:

immersing a substrate in a plating liquid containing at least one carbon structure selected from a group of fullerenes and carbon nanotubes; and

forming a metal plating layer on said ~~conductive layer~~ substrate in said plating liquid, wherein said carbon structure is stuck out from an upper portion of said metal plating layer and a part of said carbon structure is buried in said metal plating layer, and wherein said metal plating layer contains an additive material which increases resistance of said metal plating layer.

Claim 15. (Currently Amended) The [[A]] manufacturing method of field emission type cold cathode device according to claim 14, further comprising:

forming a conductive layer on a substrate before immersing said substrate.

Claim 16. (Original) The manufacturing method according to claim 14, wherein said metal plating layer is formed by either electroplating processing or electroless plating processing.

Claim 17. (Currently Amended) A manufacturing method of field emission type cold cathode device comprising:

forming a conductive layer on a first substrate having concaves;

immersing said first substrate in a plating liquid containing at least one carbon structure selected from a group of fullerenes and carbon nanotubes;

forming a metal plating layer on said conductive layer in said plating liquid, said carbon structure being stuck out from an upper portion of said metal plating layer and a part of said carbon structure being buried in said metal plating layer, and said metal plating layer containing an additive material which increases resistance of said metal plating layer.;

pressing a second substrate to said first substrate sandwiching said metal plating layer; and

removing said first substrate from said second substrate leaving said metal plating layer on said second substrate.

Claim 18. (Original) The manufacturing method according to claim 17, wherein said metal plating layer is formed by either electroplating processing or electroless plating processing.

Claim 19. (New) The manufacturing method of field emission type cold cathode device according to claim 14, wherein said additive material is selected from a group of boron, phosphorus and polytetrafluoroethylene.

Claim 20. (New) The manufacturing method of field emission type cold cathode device according to claim 17, wherein said additive material is selected from a group of boron, phosphorus and polytetrafluoroethylene.